

CBCS SCHEME

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15NT34

Third Semester B.E. Degree Examination, Jan./Feb. 2021

MOSFETS and Digital Circuits

Time: 3 hrs.

Max. Marks: 80

Note: Answer any FIVE full questions, choosing ONE full question from each module.

Module-1

- 1 a. Explain with neat diagrams the construction of JFET. Mention its characteristics. (08 Marks)
b. With the help of neat diagrams, explain n-well MOS transistor fabrication process. (08 Marks)

OR

- 2 a. Write a short note on channel length modulation and subthreshold conduction. (05 Marks)
b. Explain the VI characteristics of MOSFET. (05 Marks)
c. Explain the SOI process with its merits and demerits. (06 Marks)

Module-2

- 3 a. Explain the CMOS inverters along with power dissipation equations. (10 Marks)
b. Give the scaling factors for gate area, gate delay and saturation current. (06 Marks)

OR

- 4 a. Explain with neat diagram the realization of two input NOR and NAND gate using CMOS technology. (10 Marks)
b. Explain the AOI and OAI gate with example. (06 Marks)

Module-3

- 5 a. Discuss the working principle of CMOS positive edge triggered latch with neat diagram. (10 Marks)
b. Distinguish between latch and registers. (06 Marks)

OR

- 6 a. With neat diagram explain the operation of JK flip flop. (08 Marks)
b. Explain mux based latch. (04 Marks)
c. Define setup time and hold time. (04 Marks)

Module-4

- 7 a. Define registers. Explain SISO, SIPO and PISO shift registers. (10 Marks)
b. Design a Mod – 5 synchronous up counter using T flip flop. (06 Marks)

OR

- 8 a. Write a note on Ring and Johnson counter. (06 Marks)
b. Design a synchronous counter using JK flip flops to count the sequence 0, 1, 2, 4, 5, 6, 0, 1, 2 (10 Marks)

Important Note : 1. On completing your answers, compulsorily draw diagonal cross lines on the remaining blank pages.
2. Any revealing of identification, appeal to evaluator and /or equations written eg, 42+8 = 50, will be treated as malpractice.

